General Purpose Transistor

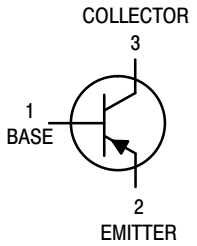
PNP Silicon

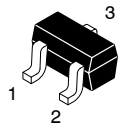
MMBT2907AWT1G, NSVMMBT2907AWT1G

These transistors are designed for general purpose amplifier applications. They are housed in the SC−70/SOT−323 package which is designed for low power surface mount applications.

Features

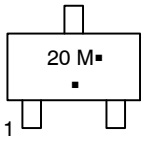
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant





SC−70/SOT−323
CASE 419−04
STYLE 3

MARKING DIAGRAM



20 = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	−60	Vdc
Collector − Base Voltage	V_{CBO}	−60	Vdc
Emitter − Base Voltage	V_{EBO}	−5.0	Vdc
Collector Current − Continuous	I_C	−600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1) T_A = 25°C	P_D	150	mW
Thermal Resistance Junction−to−Ambient	$R_{\theta JA}$	833	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. FR−5 = 1.0 x 0.75 x 0.062 in.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT2907AWT1G	SC−70 (Pb−Free)	3000 Tape & Reel
NSVMMBT2907AWT1G	SC−70 (Pb−Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 2) (I_C = −10 mAdc, I_B = 0)	$V_{(BR)CEO}$	−60	–	Vdc
Collector – Base Breakdown Voltage (I_C = −10 μAdc, I_E = 0)	$V_{(BR)CBO}$	−60	–	Vdc
Emitter – Base Breakdown Voltage (I_E = −10 μAdc, I_C = 0)	$V_{(BR)EBO}$	−5.0	–	Vdc
Base Cutoff Current (V_{CE} = −30 Vdc, $V_{EB(off)}$ = −0.5 Vdc)	I_{BL}	–	−50	nAdc
Collector Cutoff Current (V_{CE} = −30 Vdc, $V_{EB(off)}$ = −0.5 Vdc)	I_{CEX}	–	−50	nAdc
ON CHARACTERISTICS[3]				
DC Current Gain (Note 2) (I_C = −0.1 mAdc, V_{CE} = −10 Vdc) (I_C = −1.0 mAdc, V_{CE} = −10 Vdc) (I_C = −10 mAdc, V_{CE} = −10 Vdc) (I_C = −150 mAdc, V_{CE} = −10 Vdc) (I_C = −500 mAdc, V_{CE} = −10 Vdc)	H_{FE}	 75 100 100 100 50	 – – – 340 –	–
Collector – Emitter Saturation Voltage (Note 2) (I_C = −150 mAdc, I_B = −15 mAdc) (I_C = −500 mAdc, I_B = −50 mAdc)	$V_{CE(sat)}$	 – –	 −0.4 −1.6	Vdc
Base – Emitter Saturation Voltage (Note 2) (I_C = −150 mAdc, I_B = −15 mAdc) (I_C = −500 mAdc, I_B = −50 mAdc)	$V_{BE(sat)}$	 – –	 −1.3 −2.6	Vdc
SMALL– SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (I_C = −50 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	200	–	MHz
Output Capacitance (V_{CB} = −10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	–	8.0	pF
Input Capacitance (V_{EB} = −2.0 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	–	30	pF
SWITCHING CHARACTERISTICS				
Turn–On Time	(V_{CC} = −30 Vdc, I_C = −150 mAdc, I_{B1} = −15 mAdc)	t_{on}	–	45	ns
Delay Time		t_d	–	10	
Rise Time		t_r	–	40	
Storage Time	(V_{CC} = −6.0 Vdc, I_C = −150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	–	80	
Fall Time		t_f	–	30	
Turn–Off Time		t_{off}	–	100	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

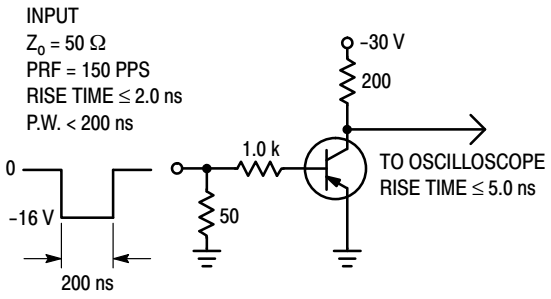


Figure 1. Delay and Rise Time Test Circuit

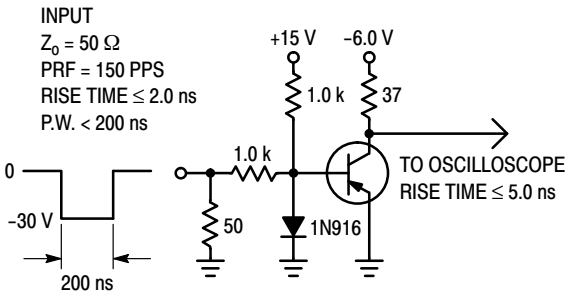


Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

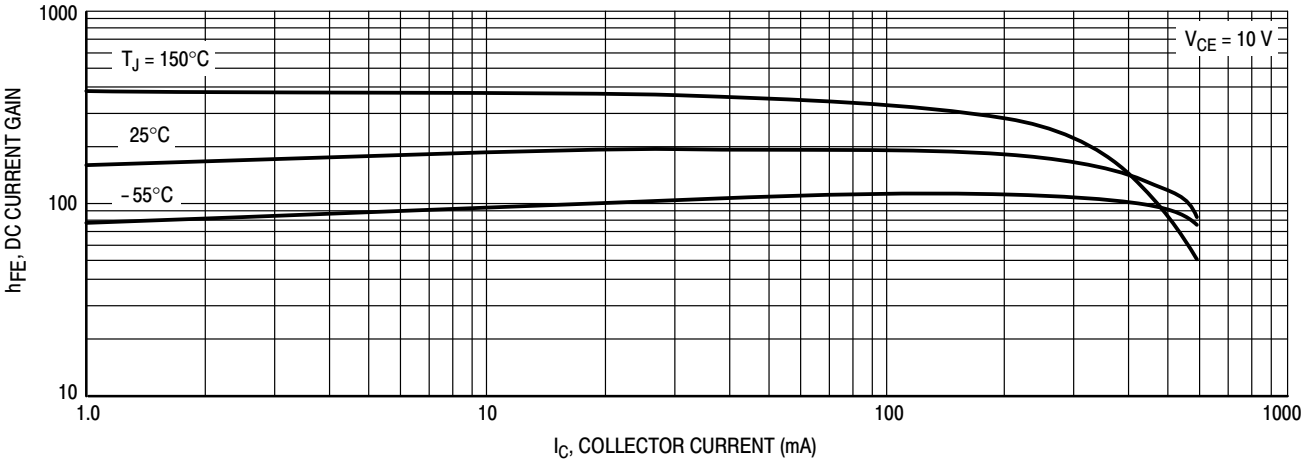


Figure 3. DC Current Gain

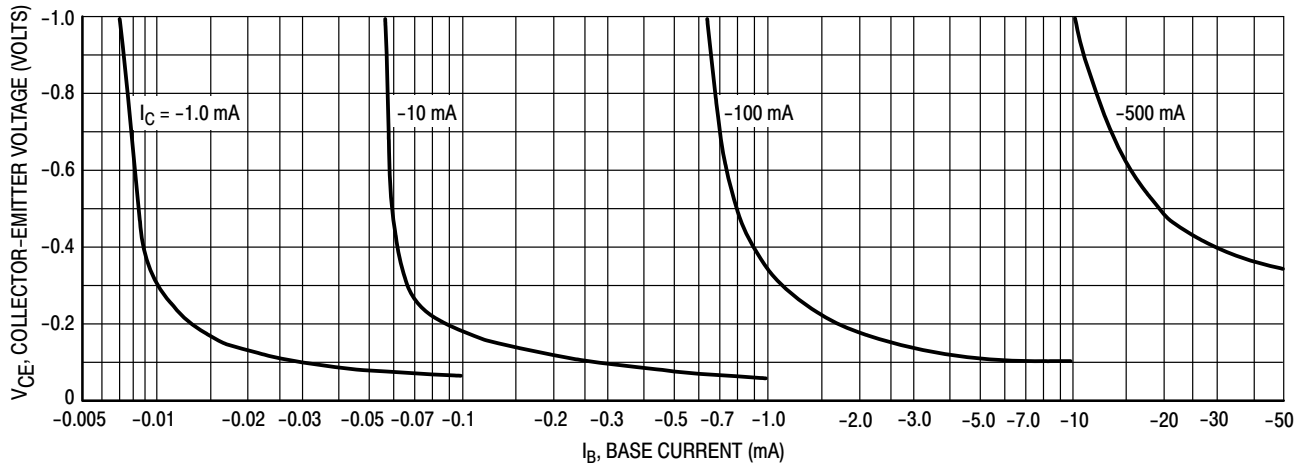


Figure 4. Collector Saturation Region

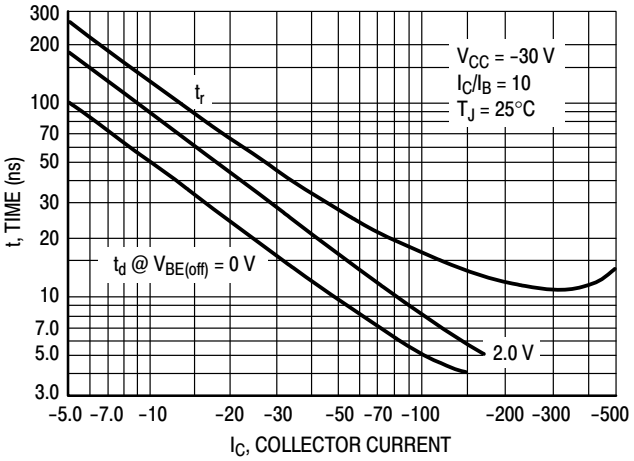


Figure 5. Turn−On Time

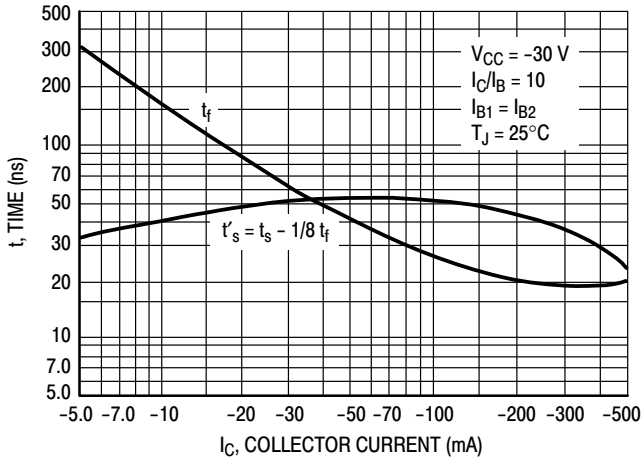


Figure 6. Turn−Off Time

TYPICAL SMALL−SIGNAL Characteristics

NOISE FIGURE

V_{CE} = 10 Vdc, T_A = 25°C

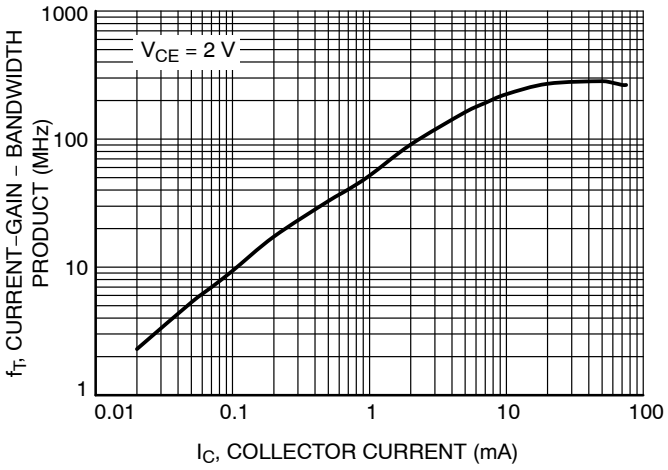


Figure 7. Current−Gain − Bandwidth Product

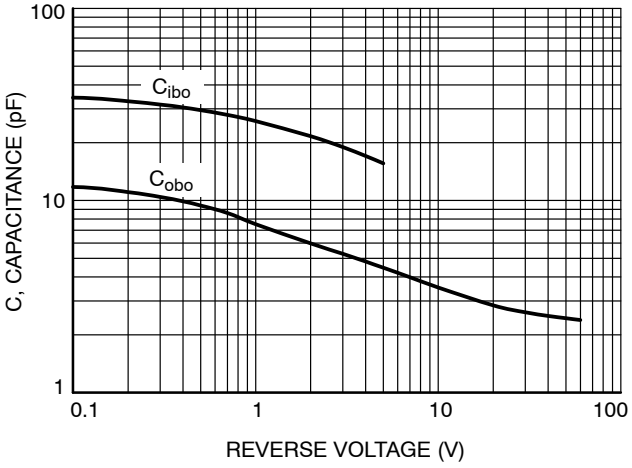


Figure 8. Capacitances

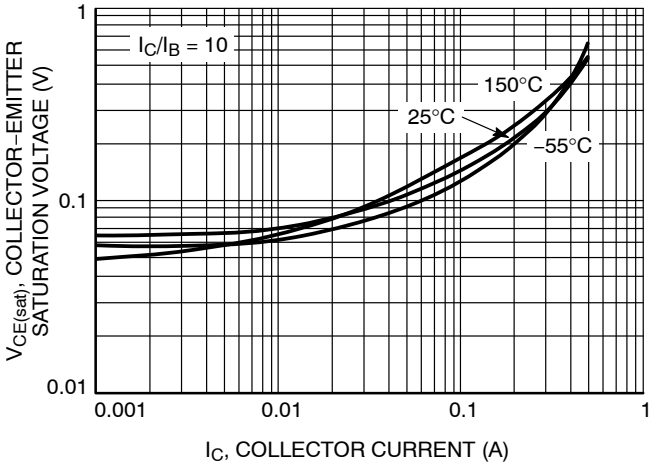


Figure 9. Collector Emitter Saturation Voltage vs. Collector Current

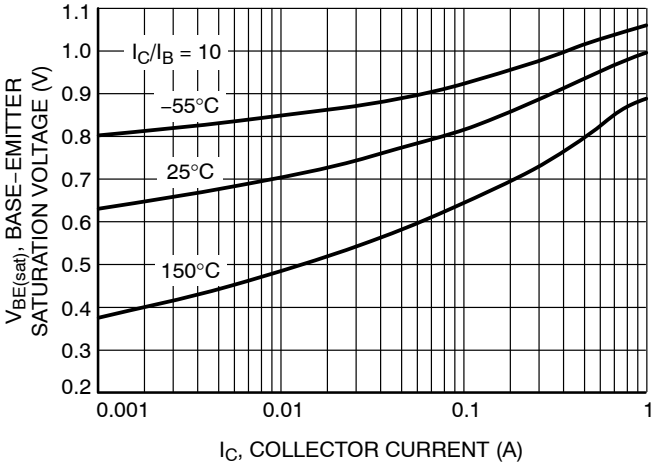


Figure 10. Base Emitter Saturation Voltage vs. Collector Current

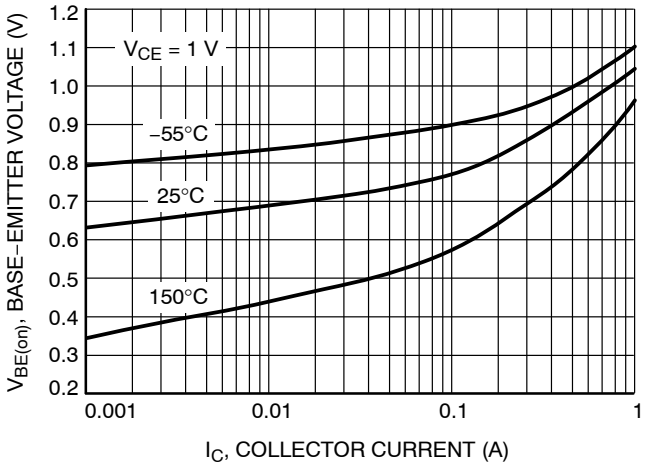
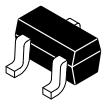


Figure 11. Base Emitter Voltage vs. Collector Current

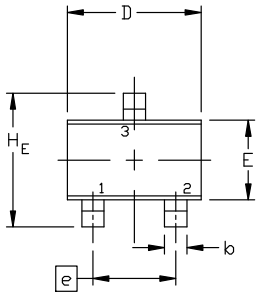
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



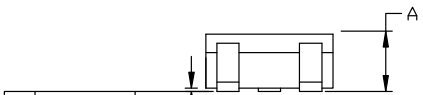
SCALE 4:1

SC−70 (SOT−323)
CASE 419
ISSUE R

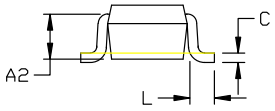
DATE 11 OCT 2022



TOP VIEW



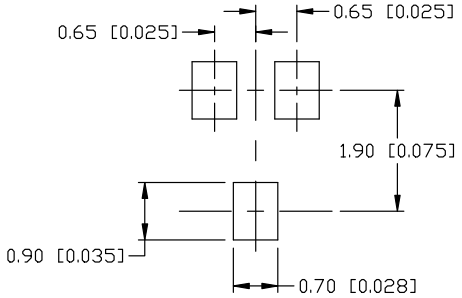
SIDE VIEW



END VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

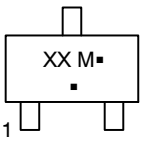
	MILLIMETERS			INCHES		
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H_E	2.00	2.10	2.40	0.079	0.083	0.095



* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

GENERIC MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
CANCELLED

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE−CATHODE

STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

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DESCRIPTION:	**SC−70 (SOT−323)**	**PAGE 1 OF 1**

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